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① 特許出願公開

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®Int. Cl.⁴

識別記号

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9発明の名称 蛍光体およびその製造方法

②特 顧 昭63-139273

②出 願 昭63(1988)6月8日

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1. 預明の名称 蛍光体およびその製造方法

- 2. 特許請求の範頭
 - 1.一般式

Zni-4MgaS: bTm

 $(0 < a \le 0.3, 0 < b \le 0.1)$

で扱され、飛体組成が破化亜鉛と硫化マグネシ ウムの固溶系からなり、主発光がTm *+により もたらされることを特徴とする蛍光体。

- 物許請求の範囲第1項記載の蛍光体において、 (0.05 < a ≤ 0.2, 0 < b ≤ 0.06)
 で扱わされることを特徴とする蛍光体。
- 3. Tm原料として、Tmの硫化物を用い、所製量のZn, Mg原料と共に900で以上で焼成することを物数とする蛍光体の製造力波。
- 4. PL (エレクトロルミネツセンス) 報子を構成する発光層の少なくとも1 収分が、特許請求の範囲第1 項記載の世光保からなることを特徴とするPL 報子。

- 5. 2n. Me. Tmの各原料がすべて硫化物で 構成され、それらを成膜することにより、特許 請求の範囲第1項記載の組成を有する蛍光体膜 を得るようにしたことを特徴とする蛍光体膜成 限用蒸発源ターゲント。
- 6. 特許請求の範囲第4項記載の第光層と、該項 光層に対して補色関係が成立する極色発光 ZnS: Mn 死光層との組み合わせからなることを特数とするEL親子。

7. 一般实

Zn:-aMgaS: bTmoMn
(O < a ≤ 0.3,0 < b ≤ 0.1,0 ≤ o ≤ 0.1)
で 込され、 母体 組成 が 硫化 延鉛 と 硫化マグネシウムの 関格系からなり、 主発光 が Tm³+により

3. 発明の詳細な説明

木箔明は、主発光が対色領域にある新規組成の 低光体ならびにその製造力法に係わり、特に自色 EL (エレクトロルミネンセンス) 炎示の背色成

もたらされることを特徴とする蛍光体。

分に用いて優れた物性を示す位光体に関する。 【世来の技術】

(Zn, Mg) Sを単体とする世光体の公知例として以下のような文献があるが、上記の単体にTm, Tm-Mnを付活した世光体に関しての公知例はない。

- 1) ジヤーナル・オブ・エレクトロケミカル・ソ サイアテイ第99巻、第4号、第155頁から 158頁 [J.Electrochomical Soc.99(4)155-158(1852)] において、MgS25モル%以下、 及り2nSから以る(2n,Mg)S母体に Cu,Ag,Ph,Ag,Sb,Biおよび Cu-Mn,Pb-Mn,Cu-Pbをそれぞ れ付活した蛍光体について、紫外線励超ならび に世子線励起による発光物性が示されている。
- 2) ジヤーナル・オブ・クリスタルグロース 第 72巻,第179页から183頁[J.of Crystal Growth 72 179-183 (1985)] において、Zni-a M g S , O < a < O . 1 の母体に50ppm の M n を付話すると、290 n m 励起により450

と報告されている。

6)特別昭51-49397 号には、赤色、緑色、青色のいずれか一色の発光尼し剥子を一枚の透明結板に形成し、残り二色の発光尼し剥子を削價の一枚の透明接板に形成し、両接板を対向して配置したことを特徴とするフルカラー移版区し剥子が開示されている。

[尭明が解決しようとする蹂躙]

上記の公知例のうち、1),2),3)はいずれも主発光が背色領域にある蛍光体であるが、発光市の単価額が70nm以上に及びカラー表示に用いる背色収分としては発度が低い。また、これらの蛍光体を出発原料に用いて作成した神殿区上剥子は全く発光しないか、発光しても傾めて輝度が低い。

一方、公知例 5)に示したと n S: T m F a の 計色死光色は彩度は高いが、 a m / w は Z n S: M n のそれより 2 桁以上低いという欠点がある。 さらにまた、公知例 6)は、 梨子構成が複雑に なる欠点がある。 nmピークの発光が頻調されたと記載されている。

- 3) ジャーナル・オブ・マテリアルサイエンス第21巻, 第2100月から2108頁 [J.of Matorial Science 21 2100-2108 (1985)] において、 ZaitaM saS: Cu, Br を用いた分散型ELの発光ピーク放長は、xの増大に伴い525nmから436nmまでシフトすると報告されている。
- 4) ラシアン・ジヤーナル・オブ・インオーガニ ツクケミストリー第9巻, 郊4報, 郊512頁か ら516頁[Russian J.of Inorganic Chemistry <u>9</u> (4)512-516 (1964)] においてM g S は 2nSに対して22モル%まで固裕し、固格無 の増大に伴い六方品系格子定数ao,Coがと もに増大すると記載されている。
- 5) '80 エス・アイ・デイ ダイジエスト第 106頁['80 SID Digest p106(1980)]
 には、神版ビレ剥子においてZnS:TmFa の2m/Wは、ZnS:Mnのそれより二桁小

本発明の目的は、上述の問題点を一路に解決した新規の世光体和成物ならびにその製造方法を促供することにある。本発明の他の目的は、白色炎 示可他な E し 親子を提供することにある。また、本発明のさらに他の目的は、上記E し 親子発光体となる 蛍光体膜の 成既に 好 遺 な 蒸 着 狐 ターゲット 机成物を提供することにある。

(旅迎を解決するための手段)

上記目的は、売光イオンに形成の高いTm³+を 川い、かつTm³+の導入をより容易ならしめるようにZnS系単体格子の拡大をはかることにより 送成される。

すなわち、水発明の蛍光体の組成は一般式

Zmi-aMgaS: bTm

で与えられ、0 < a < 0.3,0 < b <u>< 0.1</u> の範囲において最も効果的な特性が得られる。

ここで、上記組成に加えて、原料や観迎工程中 において不可違的に混入する不頼物が存在するこ とは、水発明の駆旨を逸視するものではない。

また、上記組成の蛍光体膜と、他の蛍光体膜と

原料は突施例1と同じTmF3 であり、蒸発源ターゲットは上記と同じ加圧成型焼精のプロセスを 経て作成した。

得られた移版EL剥子の5KHz、正弦故駆動下のEL飽和卸度の相対値を第1数に示した。ここで輝度基準には比較例2nS:0.01Tmを用いた。第1数から明らかなように、比較例では b=0.01,0.03,0.06 の順に輝度が単調に減少するのに対して本発明の2no.oMgo.15 母体では、b=0.03 すなわちTm濃度3モル%の時、2nS:0.01Tmの209% の即度が得られた。

ここで、上記組成物中に無初もしくは許容しう る範囲の他の不執約が存在することは本発明の要 台の範囲に含まれる。

何えば、スnraMgaS中にはMn等の不純物が固治しやすい。また、蛍光体の焼成工程あるいは添着工程においてMnが上記組成に混入することがしばしば生ずる。しかし、このようなMnの混入は、少量に止まるかぎりにおいて、本発明の

な色皮点は、上記二別宏着膜によらずとも、 2 n S : M n 蛍光体と本発明の蛍光体の同時 E B 蒸着に よつても得られた。

页 1 数

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|------------------|---------|---------|--|--|--|--|
| M g S 図 泊 量 (モル) | n = 0.0 | a = 0.1 | | | | |
| Tm減炭(モル) | [比較例] | [尖施例2] | | | | |
| b = 0.01 | 100 | 182 | | | | |
| b=0.03 | 61.0 | 209 | | | | |
| b=0.06 | 50.5 | 103 | | | | |

(発明の効果)

水発明によれば、低度原料を用いて類似発光色の

の従来蛍光体よりも

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面彩度の

発光が得

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通常の

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色温度

の、

しかも

安価

な白色

表示

が

位光体の特性劣化を激起しない。また、無視し得ない量のMnが存在する場合においても、Mnの存在 (例えば10モル%程度)に伴う発光が、 尼L滑子等の白色表示に対して阻密契因とならない範囲においては、無視しうるものと同様に扱うことができる。

尖施钢3

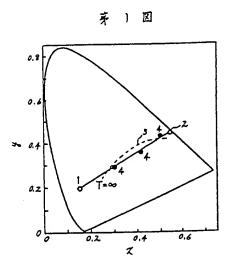
得られるなどの効果があり被品パンクライトに好 遊である。

なお、本発明の効果は主発光がTm *+でもたら される新規世光体組成物で得られるものであるが、 Tm *+以外の希土戴イオンが微量導入されていて も発明の効果が摂われることはない。

4. 國面の簡単な説明

第1 図は本発明の実施例の蛍光体の色度特性を 示す色度図である。

代班人 办理士 小川历



- ノ 冬発明の営光体の色展点 Z ZNS: HN営光体の色展点
- 4 実施例39EL素子の色度点

(12) Public Patent Report (A)

HEI 1-311188

(51) Int. Cl.⁴ C 09 K 11/56 H 05 B 33/14

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Phosphor material and the manufacturing method of the phosphor material

(54) Name of invention

(21) Application Number

TOKUGAN SHO 63-139273

(22) Application Date

June 8, 1988

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Details

1. Name of invention

Phosphor material and the manufacturing method of the phosphor material

2. Range of the patent claim

1) It is a phosphor material, which features that the main emission is generated by Tm³⁺, which the ordinary formula is indicated below, and

$$Z n_{1-a} M g_a S : b T m$$

(0 < a \leq 0.3, 0 < b \leq 0.1)

which the main composition is made of the solid solution related to zinc sulfate and magnesium sulfate.

2) It is concerning the phosphor material, which is stated in the aforementioned (1) of the range of the patent claim, and it is a phosphor material, which features that the numbers are indicated as below;

$$(0.05 < a \le 0.2, 0 < b \le 0.06)$$

- 3) It is a manufacturing method of phosphor material, which features that the main material is made of T m, and the baking is performed with the designated amount of Zn and Mg raw material at 900 °C or higher.
- 4) It is an EL element, which features that at least one component of the emission layer, which composes the EL element, is made of the phosphor material, which is mentioned in (1) of the range of the patent claim.

- 5) It is an evaporation source target for the phosphor material film forming, which features that it shall obtain the phosphor material film, which shall include the composition of (1) of the range of the patent claim by forming each raw material of Zn, Mg and Tm, which are constructed by the sulfide.
- 6) It is an EL element, which features that the combination of the structure is made of the emission layer, which is mentioned in (4) of the range of the patent claim, and the orange emitting ZnS: Mn emission layer, which shall have the relationship of the complementary colors to the said emission layer.
- 7) It is a phosphor material, which features that the main emission is generated by Tm ³⁺, which the ordinary formula is indicated below, and

$$Z n_{1-a} M g_a S : b T m o M n$$

(0 < a \leq 0.3, 0 < b \leq 0.1, 0 \leq c \leq 0.1)

which the main composition is made of the solid solution related to zinc sulfate and magnesium sulfate.

3. Detailed explanation of the invention

[Utility field of the industry]

This invention is related to the phosphor material of the new composition, which the main emission is within the blue color area, and the manufacturing method of such phosphor material, and it is specially related to such phosphor material, which shows an excellent characteristic for using it in the blue color area of the white color EL display.

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[Existing technique]

There are publications according to the phosphor material, which shall have the (Zn, Mg) S as the main material and the examples are shown below. However, there are no publications concerning the phosphor material, which the Tm and Tm – Mn are added to the said main material.

- 1) The emitting characteristics of the ultraviolet light excitation and the electron beam excitation concerning the phosphor material, which Cu, Ag, Pb, As, Sb, Bi, Cu Mn, Pb Mn and Cu Pb are added to the main material of (Zn, Mg) S, which is composed of MgS less than 25 mol% and ZnS, were written on page 155 to page 158, Vol. 99 (4) of the Journal of Electrochemical Society (1952).
- 2) The emitting at 450nm peak was observed by 290nm excitation by adding Mn of 50 ppm to the main material of Zn_{1-a} M g S, 0 < a < 0.1, which were mentioned on page 179 to page 183, Vol. 72 of the Journal of Crystal Growth (1985).
- 3) It is reported that the emission peak wavelength of the scattered EL, which shall use Z n_{1-a} M g_a S: C u, B r, shall be shifted from 525nm to 436 nm, on page 2100 to page 2108, Vol. 21 of the Journal of Material Science (1985).

- 4) Page 512 to page 516, Vol. 9 (4) of the Russian Journal of Inorganic Chemistry mentioned that the MgS shall solidly dissolve up to 22 mol% against the ZnS, and when the amount of the solid solution increases, a o and C o of the hexagonal grid invaluable shall also increase.
- 5) In the '80 S I D Digest, Page 106 (1980), concerning the thin film element, lm/W of Z n S: T m F₃ is 2 digits smaller than the lm/W of the Z n S: M n.
- 6) In the KOKUKAISHO 61-49397, it indicates such full-color thin film EL element, which features that it consists of 2 substrates, which are the transparent substrates that one of the emitting EL elements of red, green or blue, is formed on, and another transparent substrate, which the emitting EL element of the remaining two colors are formed on, and that both substrates are arranged at the facing way to each other.

[The problem to be solved by the invention]

According to the abovementioned publications, the main emitting areas of the phosphor materials, which are mentioned in (1), (2) and (3) are all within the blue area, however, because the half value range of the emitting band is more than 70nm, the luminance is low as for the blue component of the color displays. Also, the thin film EL element, which is created using these phosphor materials, might not generate emission at all or even if they do, the luminance shall be extremely low.

On the other hand, although the luminance of the Z n S: T m F 3, which is mentioned in the above (5), is high, lm / W is more than 2 digits lower than Z n S: M n, which is a weak point. Also, the abovementioned (6) has a weak point in that the element structure shall be complicated.

The purpose of this invention is to provide the new phosphor composition material, which shall solve all the problems mentioned above, and the manufacturing method of such phosphor material. The other purpose of this invention is to provide the EL element, which is possible to make the white displays. Also, one other purpose of this invention is to provide the evaporation source target composition material, which is suitable for forming the phosphor film of the abovementioned EL element phosphor material.

[The method of how to solve the problem]

The above purpose shall be accomplished by using the Tm³⁺ with high luminance against the emitting ion as well as expanding the Z n S related main grid in order to make it easy to introduce the Tm³⁺.

Therefore, the composition of the phosphor of this invention is indicated by the ordinary formula of Z n _{1-a} M g _a S : b T m, and it shall obtain the most effective characteristics within the range of 0 < a < 0.3, $0 < b \le 0.1$.

In addition to the abovementioned composition, the fact that there are impurities, which are mixed during the manufacturing process, etc., they shall not cause deviation from the purpose of the invention.

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Also, by combining the phosphor film of the abovementioned composition and other phosphor film, an excellent white display EL element can be created.

As universally known, because the ion radius of Z n $^{2+}$ is r = 0.74 °A is smaller than the ion radius of Tm $^{3+}$ of r = 0.95 °A, in order to introduce a designated amount of Tm $^{3+}$, it is necessary to expand the main grid. In order to expand the main grid, one should dissolve ZnS into MgS. For example, if 22 mol% MgS is dissolved into ZnS, the grid invaluable ao is increased by 1.9% and the grid invaluable Co is increased by 1.1%.

Also, in order to introduce the emitting ion of the triple positive charge such as Tm ³⁺ to the positive ion grid point of the double positive charge such as Zn ²⁺ and Mg ²⁺, instead of using Tm element, which is widely used, it is possible to use sulfuric raw material of Tm or cheap oxide raw material. By using the evaporation source target of the combination of the abovementioned sulfuric raw material, the white display EL element shall be created effectively.

[Function]

The most important advantage of this invention is that the same level or even higher luminance as the ZnS: 0.001 Tm, which the initial material is Tm F_3 , is obtained by Z n $_{0.8}$ M g $_{0.1}$ S: 0.001 Tm, which the initial material is T $_{2}$ O $_{3}$, which is a cheaper material.

Also, the second advantage is that by expanding the main grid from ZnS to (Zn, Mg) S, the adjustment of Tm density to make the suitable luminance becomes easier. This advantage is good for the adjustment of the Tm density within the emission layer of then thin film EL element, which makes the upper limit of the Tm density within the emission layer at least one digit higher than the existing number.

The third advantage is that by using sulfuric Tm instead of TmF₃ as the initial material, stable EB deposition can be performed without having any charge ups.

The abovementioned second and third advantages, which are related to the thin film EL element forming, shall generate the fourth advantage as well. It means by combining the blue emission layer with the optimum condition of the Tm density and well-known ZnS: Mn orange emission layer, such white EL display as the color temperature of 3000K to 9000K can be possible. When the amount of MgS solid solution against ZnS is increased, a weak broad emitting appears in the orange color area besides the main emitting within the blue color area, and because this emitting shall be overlapped with the ZnS: Mn orange color emitting, it shall not bother the white display.

[Example of implementation]

Hereinbelow, this invention shall be explained in accordance with the implementation example.

Implementation example 1

According to the ordinary formula of Zn 1-a MgaS: b Tm, in order to compose the phosphor material of a = 0.15, b = 0.001 which means $Zn_{0.35}$ Mg_{0.15} S: 0.001 T m, the initial material of ZnS, MgS and Tm2 O3 with high purity shall be measured accurately, and shall be mixed them well, and after mixing, 100 g of them shall be placed on the transparent quartz board, and then they shall be baked at 1000 °C for 2 hours at the atmosphere of H₂S flow rate of 100 ml/min. Also, for the comparative example, Tm F₃ is used for the initial raw material, which is commonly used for a = 0, b = 0.001, which means ZnS: 0.001 Tm, and baked under the exact same firing conditions as the above. The luminance by the electron beam excitation of 10 KV, 1 μ A / cm² was 119% setting the standard figure as the figure of the comparative example when using the phosphor When b = 0.001, the luminance which is higher than the material of a = 0.15. comparative example is obtained at x = 0.05, 1.0 and 2.0 of the chromaticity coordinates. On the other hand, when a > 0.3, because the association coloring appeared, which shall be the reason of the sludge of M g S, such luminance, which is equal to the comparative example, could not be obtained. Tm₂ O₃ is a cheaper material than Tm F₃, and it is a better material as for the utility phosphor material.

Implementation example 2

A 3-layer structured thin film EL element, which the emission layer is sandwiched between the Y₂ O₃ insulation layers, is created by the EB deposition technique. The phosphor material of this invention and the ZnS: T m phosphor material of the comparative example are used for the emission layers. According to the phosphor composing of this invention, sulfuric Tm, which the sulfate rate is 93% from sulfurating Tm₂ O₃ for 45 hours at the atmosphere of H₂S 100 ml / min., is used for the initial material of Tm in order to control the charge up when performing the EB deposition. Therefore, unlike the implementation example 1, all of the Zn, Mg and Tm raw materials are sulfuric, and the evaporation source target for EB was created by firing at 1000 °C at the Algon atmosphere after applying the pressure molding on the powder phosphor material, which is obtained by baking the mixture of each designated amount of Zn, Mg and Tm material for 2 hours at 900 to 1000 °C at the H₂S flow rate of 100 ml / min.

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On the other hand, the initial material of Tm concerning the comparative example of ZnS: Tm is Tm F₃, which is the same as the implementation example 1, and the evaporation source target is created by the same process as the abovementioned pressured molding baking.

The relative value of the EL saturated luminance under the sine wave drive at 5 KHz of the obtained thin film EL element is shown in Table 1. The comparative example of ZnS: 0.01 Tm is used for the luminance standard. As it is clearly seen from Table 1,

compared with the result of the comparative example, which the luminance decreases from b=0.01 to 0.03 and then to 0.06 when b=0.03, which means Tm density is 3 mol%, 209% luminance of ZnS: 0.01Tm is obtained from the Zn 0.9 Mg 0.1 S main material of this invention.

The existence of the impurities within the abovementioned composition, which can be ignored or within the acceptable range, shall be included in the range of this invention. For example, the impurities of Mn, etc., are easily dissolved in the Zn_{1-a} Mg_aS. Also, Mn often shall be mixed with the abovementioned composition during the firing process of the phosphor material or deposition process. However, such mixture of the Mn shall not bring the quality inferior to the phosphor material as long as it stays within the certain amount, and if the emitting from the existence of Mn (for example 10 mol%) shall not be the reason for an impediment against the white color display of the EL element, etc., it can be treated as the same case, which can be ignored.

Implementation example 3

The thin film EL element, which the emission layer is sandwiched by the same insulation film Y_2 O_3 as the implementation example 2, which is made of the 2-layer density film, which is composed of the ZnS: Mn, which the film thickness of the emission layer is 0.30 μ m and the peak wavelength is 585 nm, and the Zn $_{0.8}$ Mg $_{0.1}$ S: 0.33 Tm of this invention, which has the film thickness of 0.81 μ m and the peak wavelength of 475 nm, is created by the EB deposition technique. By the sine wave drive of 5KHz, the day light color emitting of the color temperature of 6500K, x = 0.307 and y = 0.290 were obtained. Also, by selecting the film thickness of the abovementioned 2-layer density layer to be 0.45 μ m, in the case of ZnS: Mn, and 0.62 μ m, in the case of the phosphor material of the invention, x = 0.410, y = 0.365, and the color temperature of 3400K, warm white color emitting was obtained. One example of the obtained chromaticity point is shown as the black points (symbol 4) in Figure 1. The similar chromaticity point is obtained also by the simultaneous implementation of EB deposition technique to the ZnS: Mn phosphor material and the phosphor material of this invention even if it does not depend on the abovementioned 2-layer density film.

As it is clearly seen from Figure 1, the black points are arranged almost in a straight line, and the white display, which is obtained by this method shows that it is a low dimension white color, which is low cost and essentially different from the white display, which is composed of the mixture of the red color, green color and blue color.

Table 1 (P.632)

| | M g S solid | a = 0.0 | a = 0.1 |
|------------|-----------------------|-----------------------|----------------------------|
| | Solution Amount (mol) | [Comparative example] | [Implementation example 2] |
| Tm density | | | |
| (mol) | | | |
| b = 0.01 | | 100 | 182 |
| b = 0.03 | | 61.0 | 209 |
| b = 0.06 | | 50.5 | 103 |

[Effectiveness of the invention]

According to the invention, not only does this obtain higher luminance and higher tint, but also it obtains wide color temperature, which is suitable for the thin film EL element of the ordinary structure, as well as the low cost white display, which is excellent for the liquid back light.

Further, the effectiveness of the invention is obtained by the new phosphor material composition, which is made of T m ³⁺, however, the effectiveness of the invention shall not change even if a small amount of ion besides T m ³⁺ is mixed.

4. Simple explanation of the figure

Figure 1 is a chromaticity diagram, which indicates the chromaticity characteristics of the phosphor material of the implementation examples of the invention.

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Figure 1

- 1: Chromaticity point of the phosphor material of the invention
 2: Chromaticity point of the ZnS: Mn phosphor material
 3: Locus of the black points
 4: Chromaticity point of the EL element of the implementation example 3

End